1. Scope :

1-1. This specification applies to N channel depletion MOSFET chips,
Device no. PM-0303A

2. Structure :

2-1. Planar type.
2-2. Electrodes.
Source : Aluminum alloy .
Gate : Aluminum alloy .
Drain : Gold alloy.

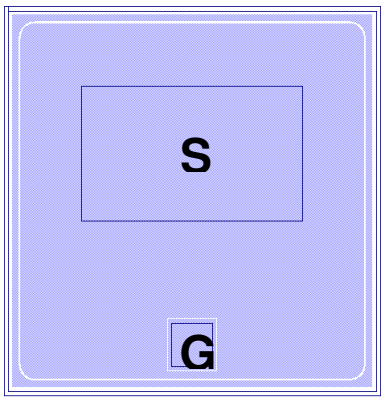
3. Size :

3-1. Chip size : 44 mils ×44 mils (1.120 mm ×1.120 mm).
3-2. Chip thickness : 12 ±1.5mils (0.305± 0.038mm).
3-3. Pad size :
Source : 26.0 mils × 15.4 mils (0.660 mm × 0.390mm).
Gate : 4.9 mils × 5.0 mils (0.124mm × 0.127 mm).
3-4. Pattern drawing : Refer to the attached drawing.

4. Absolute maximum rating (Ta = 25 ℃)

Parameter	Symbol	Rating	Unit
Continuous drain current v_{GS}=0v	$I_{D(m)}$	0.3	A
Drain-source Voltage	V_{DSS}	60	V
Gate-source Voltage	V_{GS}	±10	V
Operating junction and storage temperature range	Tj T_{STG}	-40to+150	℃

Pattern drawing



5. Electrical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain to source breakdown voltage	BV_{DSS}	V_{GS} =-5V I_{DS} = 100uA	60			V
Gate to source off voltage	$V_{GS(off)}$	V_{DS} = 25V I_{DS} =10uA	-1.0	-1.6	-2.3	V
Gate to source leakage current	I_{GSS}	V_{GS} = ±10V V_{DS} = 0V		± 0.07	± 1	μA
Drain to source leakage current	$I_{D(OFF)}$	V_{GS} =-5V V_{DS} = 60V			1	μA
Drain to source on resistance	$R_{DS(on)}$	V_{GS} = 0V I_D = 100mA		0.6	1.0	Ω
Diode forward voltage drop	V_{SD}	V_{GS} =-10V I_{SD} = 100mA		0.84	1.8	V